Notice of References Cited

Application/Control No.	Applicant(s)/Pater	nt Under
10/564,486	Reexamination SON, HYO-KUN	
Examiner	Art Unit	
JESSE Y. MIYOSHI	2811	Page 1 of 1

U.S. PATENT DOCUMENTS

SIST AT LETT BY SOME TO					
*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	Α	US-2003/0006418	01-2003	Emerson et al.	257/79
*	В	US-2002/0175341	11-2002	Biwa et al.	257/103
*	С	US-5,684,309	11-1997	McIntosh et al.	257/191
*	D	US-2004/0155248	08-2004	Fukuda et al.	257/079
*	Е	US-6,614,059	09-2003	Tsujimura et al.	257/101
	F	US-			
	G	US-			
	Н	US-			
		US-			
	J	US-			
	К	US-			
	L	US-			
	м	US-			

FOREIGN PATENT DOCUMENTS

	FOREIGN FATERY DOCUMENTS					
*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO03005459	01-2003	International A	Yoshikatsu Fukuda	H01L21/285
	0					
	Р					
	Q					
	R					
	s					
	т					

NON-PATENT DOCUMENTS

		NORTH ATENT DOGGLETTO
*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kenji Uchida et al., "Photoluminescence Characteristics and Pit Formation of InGaN/GaN quantum-well structures grown on sapphire substrates by low-pressure metalorganic vapor phase epitaxy", Nov. 17 1998, Journal of Electronic Materials, vol. 28 No.3, 1999, pages 246-251.
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A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.